

## 1. General description

Planar passivated four quadrant triac in a SOT404 (D2PAK) surface-mountable plastic package intended for use in general purpose bidirectional switching and phase control applications.

### 2. Features and benefits

- High blocking voltage capability
- Less sensitive gate for improved noise immunity
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants

### 3. Applications

- General purpose motor control
- General purpose switching

### 4. Quick reference data

Table 1. Quie	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \text{ Fig. 4}; \text{ Fig. 5}$	-	-	65	A
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 102 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	8	A
Static characte	eristics					
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	5	25	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	25	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	11	25	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>	-	30	70	mA

# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2
2	T2	main terminal 2		sym051
3	G	gate		
mb	T2	mounting base; main terminal 2	D2PAK (SOT404)	

# 6. Ordering information

Table 3. Ordering in	formation					
Type number	Package					
	Name	Description	Version			
BT137B-600F	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

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# 7. Limiting values

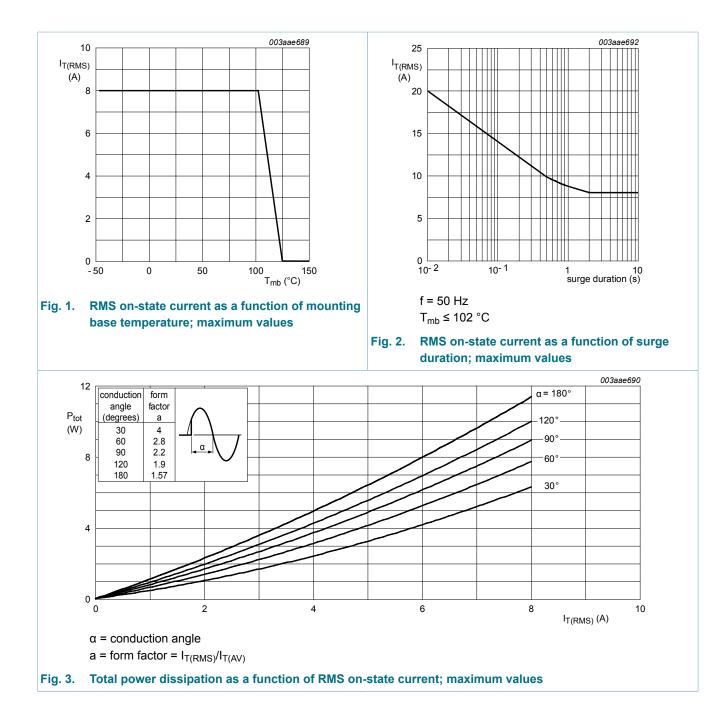
#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 102 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	8	A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; Fig. 4; Fig. 5$	-	65	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	71	A
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	21	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T$ = 12 A; $I_G$ = 0.2 A; $dI_G/dt$ = 0.2 A/µs; T2+ G+	-	50	A/µs
		I <sub>T</sub> = 12 A; I <sub>G</sub> = 0.2 A; dI <sub>G</sub> /dt = 0.2 A/μs; T2+ G-	-	50	A/µs
		I <sub>T</sub> = 12 A; I <sub>G</sub> = 0.2 A; dI <sub>G</sub> /dt = 0.2 A/μs; T2- G-	-	50	A/µs
		I <sub>T</sub> = 12 A; I <sub>G</sub> = 0.2 A; dI <sub>G</sub> /dt = 0.2 A/μs; T2- G+	-	10	A/µs
I <sub>GM</sub>	peak gate current		-	2	А
P <sub>GM</sub>	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

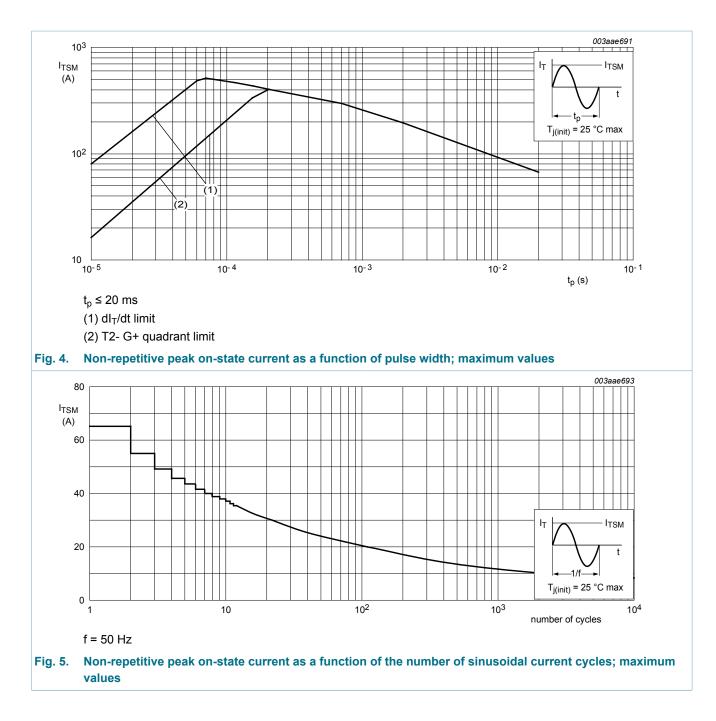
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### 8. Thermal characteristics

Table 5. T	hermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	half cycle; <u>Fig. 6</u>	-	-	2.4	K/W
	from junction to mounting base	full cycle; <u>Fig. 6</u>	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	PCB (FR4) mounted; minimum pad sizes	-	55	-	K/W

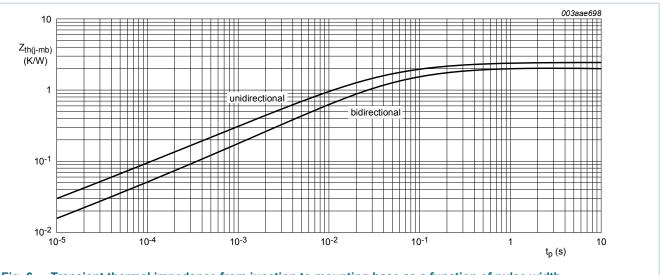


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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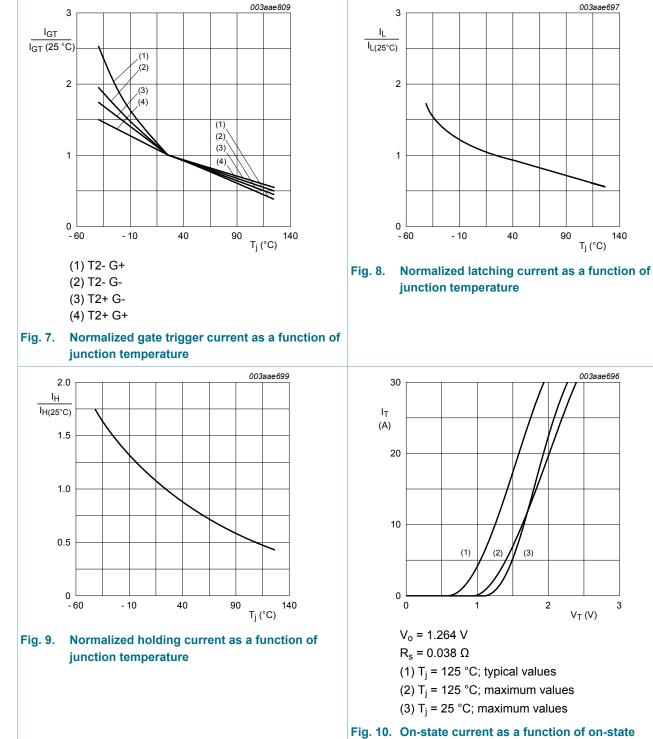
## 9. Characteristics

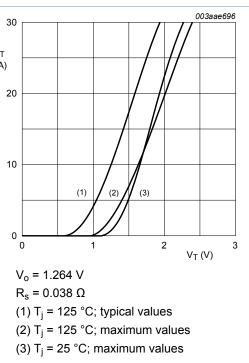
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics	I I				
I <sub>GT</sub>	gate trigger current	$V_D$ = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; Fig. 7	-	5	25	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	8	25	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	11	25	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	30	70	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	7	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	16	45	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T <sub>j</sub> = 25 °C; Fig. 8	-	5	30	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T <sub>j</sub> = 25 °C; Fig. 8	-	7	45	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	5	20	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.65	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.7	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
l <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	aracteristics	11				
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit	50	250	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; T <sub>j</sub> = 95 °C; dI <sub>com</sub> /dt = 3.6 A/ ms; I <sub>T</sub> = 8 A; gate open circuit	-	20	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 12 A; V <sub>D</sub> = 600 V; I <sub>G</sub> = 0.1 A; dI <sub>G</sub> / dt = 5 A/µs	-	2	-	μs

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40

90

140

Tj (°C)

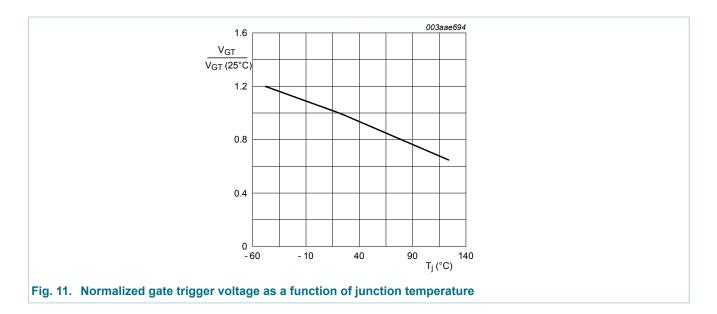
Fig. 10. On-state current as a function of on-state voltage

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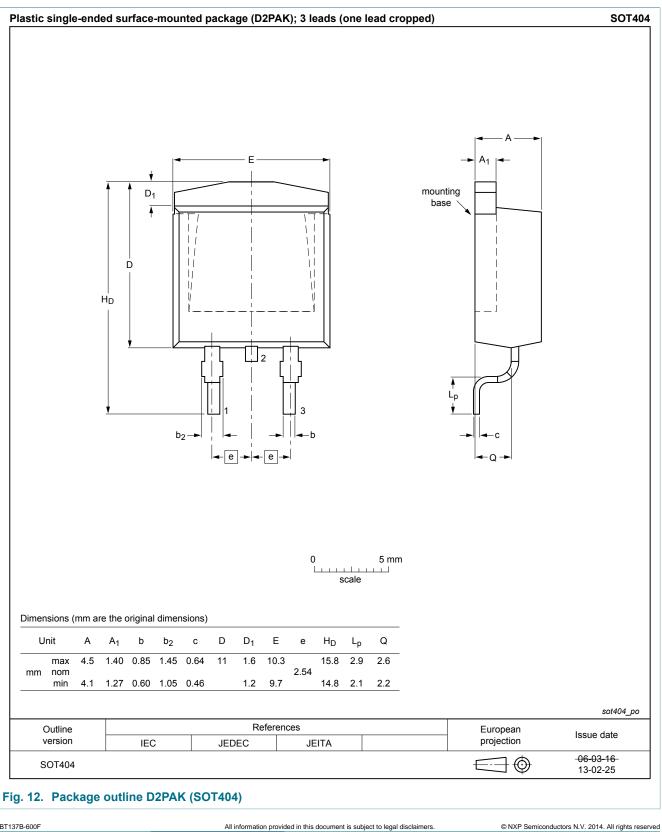
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### 10. Package outline



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### 11. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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